NSN 5961-01-012-4270

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-012-4270 **Inclosure Material:** Metal **Overall Length:** 0.394 inches **Overall Diameter:** 0.408 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-59 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.430 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 120.0 breakdown voltage, collector-to-base, emitter open and 6.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 5.00 amperes source cutoff current and 2.00 amperes source cutoff current **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 3 tab, solder lug Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

NSN 5961-01-012-4270 Transistor - Page 2 of 2



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